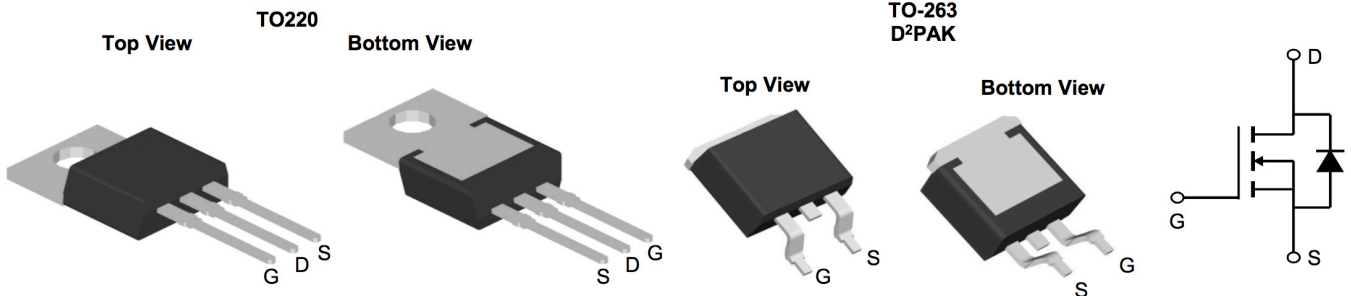


### Features

- 500V/18A,  
 $R_{DS(ON)}=340m\Omega(Typ.)@V_{GS}=10V$
- 100% avalanche tested
- 175°C Operating Temperature
- Lead Free and Green Devices Available (RoHS Compliant)
- Motor Drive
- Uninterruptible Power Supply
- DC/DC converter
- General Purpose Application



### Pin Configurations



### Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
XPX18N50TU	TO-263-3	XPX18N50TU XXX YYYY	800

### Absolute Maximum Ratings (T<sub>c</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>DSS</sub>	Drain-Source Voltage (V <sub>GS</sub> = 0V)	500	V
I <sub>D</sub>	Continuous Drain Current	18	A
I <sub>DM</sub>	Pulsed Drain Current (note1)	58	A
V <sub>GS</sub>	Gate-Source Voltage	±30	V
E <sub>AS</sub>	Single Pulse Avalanche Energy (note2)	452	mJ
I <sub>AR</sub>	Avalanche Current (note1)	14	A
E <sub>AR</sub>	Repetitive Avalanche Energy (note1)	60	mJ
P <sub>D</sub>	Power Dissipation (T <sub>c</sub> = 25°C)	32	W
T <sub>J</sub> , T <sub>stg</sub>	Operating Junction and Storage Temperature Range	-55~+150	°C
R <sub>thJC</sub>	Thermal Resistance, Junction-to-Case	4.12	°C/W
R <sub>thJA</sub>	Thermal Resistance, Junction-to-Ambient	62.5	°C/W

**Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)**

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
BVDSS	Drain-Source Breakdown Voltage	VGS = 0 V, ID = 250 μA	500	550		V
ΔBVDSS/ ΔTJ	Breakdown Voltage Temperature Coefficient	ID = 250 μA, Referenced to 25°C		0.52		V/°C
IDSS	Zero Gate Voltage Drain Current	VDS=500 V, VGS=0V			1	μA
		VDS=400 V, TC=125°C			10	μA
IGSSF	Gate-Body Leakage Current, Forward	VGS= 30V, VDS=0 V			100	nA
IGSSR	Gate-Body Leakage Current, Reverse	VGS=-30 V, VDS=0V			-100	nA
VGS(TH)	Gate Threshold voltage	VDS=VGS, ID=250 uA	2.0	3.0	4.0	V
RDS(On)	Drain-Source on-state resistance	VGS=10V, ID = 6.5A, T <sub>J</sub> = 25°C		340	400	mΩ
gFS	Forward Transconductance	VDS = 40 V, ID=6.5A (Note 4)		12.8		S
Ciss	Input capacitance	VDS=25V, VGS=0V, f=1.0MHz		1651		pF
Coss	Output capacitance			188		pF
Crss	Reverse transfer capacitance			7		pF
td(on)	Turn On Delay Time	VDD= 250 V, ID = 16 A, RG = 25 Ω		31		ns
tr	Rising Time			43		ns
td(off)	Turn Off Delay Time			106		ns
tf	Fall Time			46		ns
Qg	Total Gate Charge	VDS = 400 V, ID = 13 A, VGS = 10 V		23.5		nC
Qgs	Gate-Source Charge			6.9		nC
Qgd	Gate-Drain Charge			7.4		nC
ISM	Maximum Pulsed Drain-Source Diode Forward Current				52	A
VSD	Diode Forward Voltage	VGS= 0 V, IS = 13 A			1.2	V
trr	Reverse Recovery Time	VGS = 0 V, IS = 13 A, dIF / dt = 100 A/μs Note 4)		340		ns
Qrr	Reverse Recovery Charge			2.8		μC

**Note :**

- 1、 The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2、 The EAS data shows Max. rating . L=4.1Mh IAS=14A, VDD=50V, RG=25Ω, Starting T<sub>J</sub> = 25 °C
- 3、 The test condition is Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 1%
- 4、 The power dissipation is limited by 150°C junction temperature
- 5、 The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

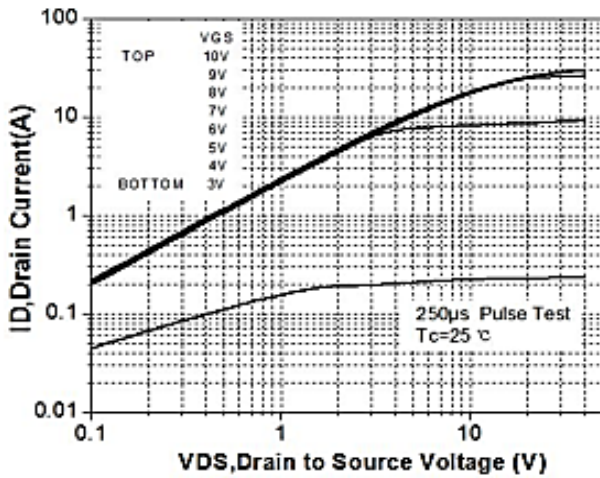


Figure 1. On-Region Characteristics

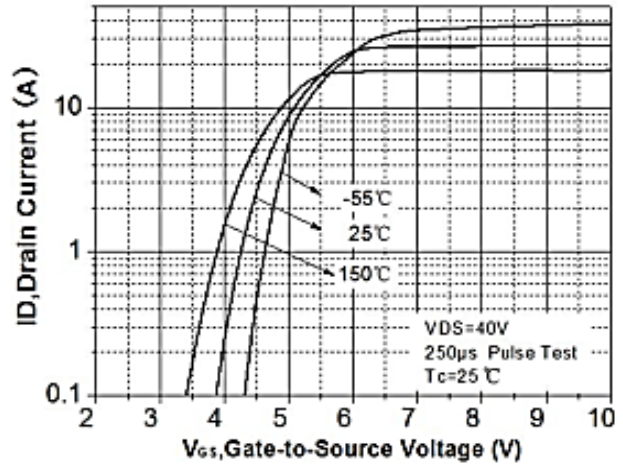


Figure 2. Transfer Characteristics

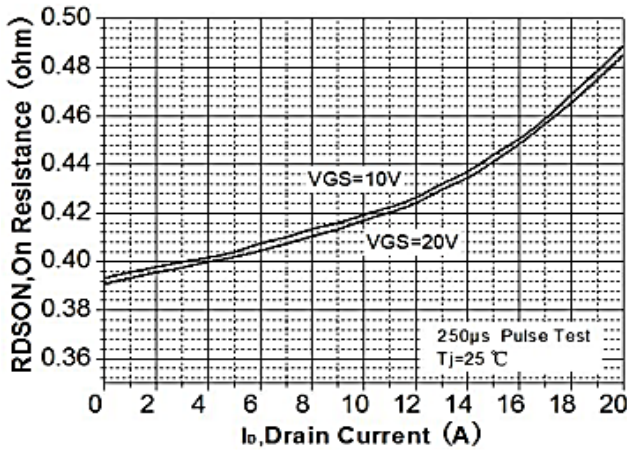


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

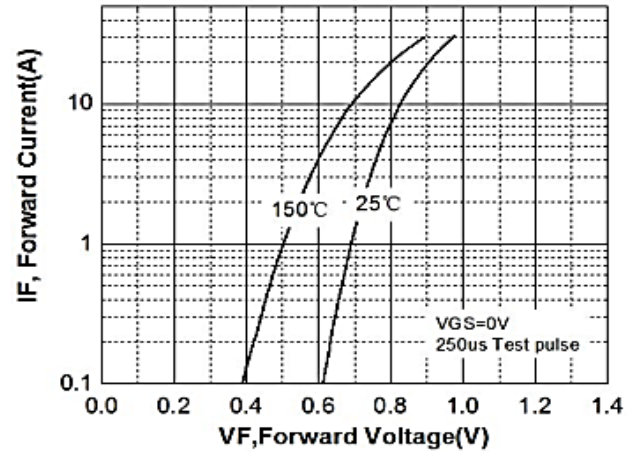


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

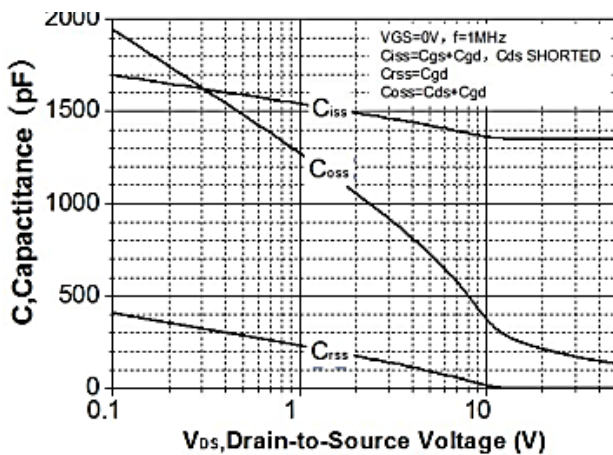


Figure 5. Capacitance Characteristics

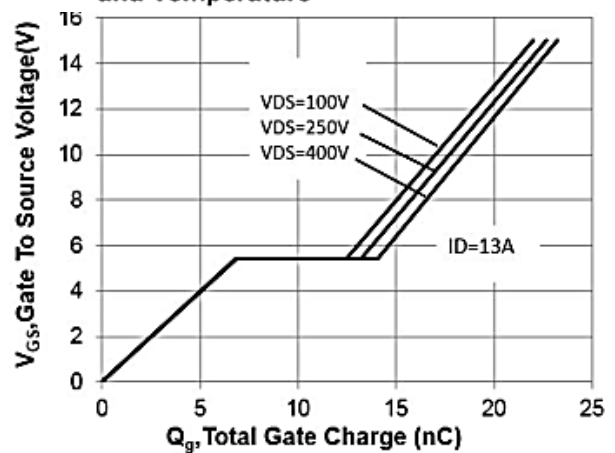


Figure 6. Gate Charge Characteristics

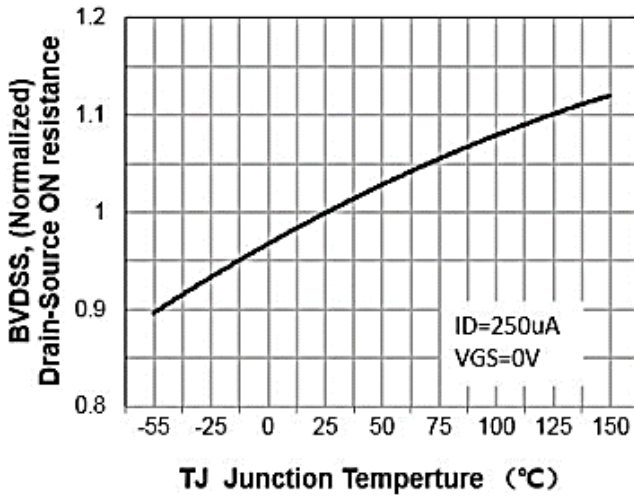


Figure 7. Breakdown Voltage Variation vs Temperature

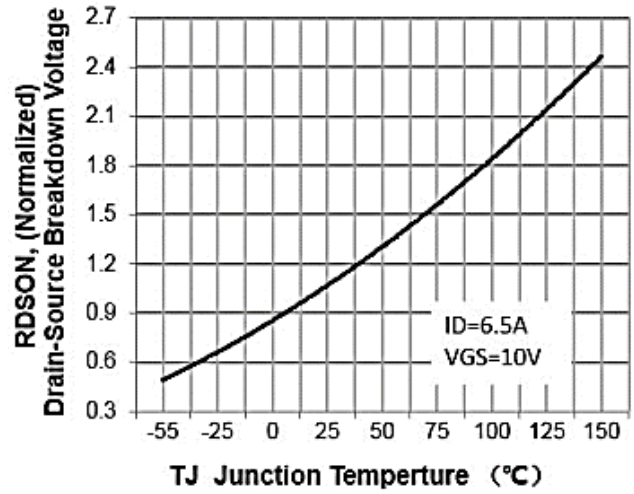


Figure 8. On-Resistance Variation vs Temperature

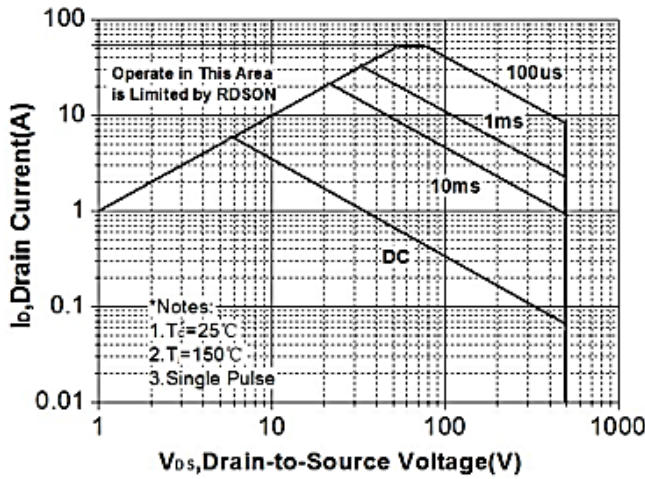


Figure 9. Maximum Safe Operating Area

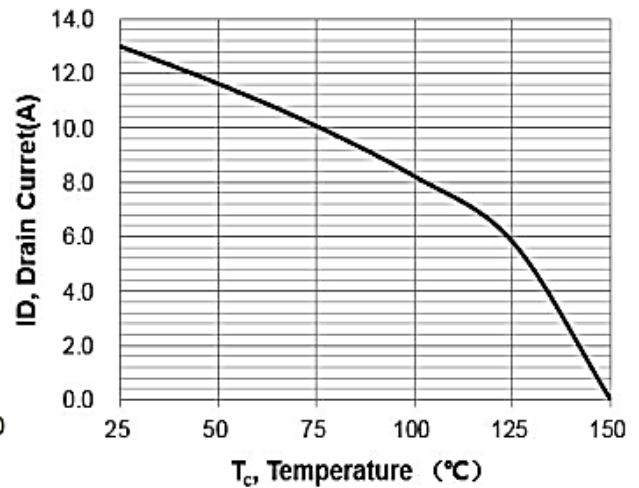


Figure 10. Maximum Drain Current vs Case Temperature

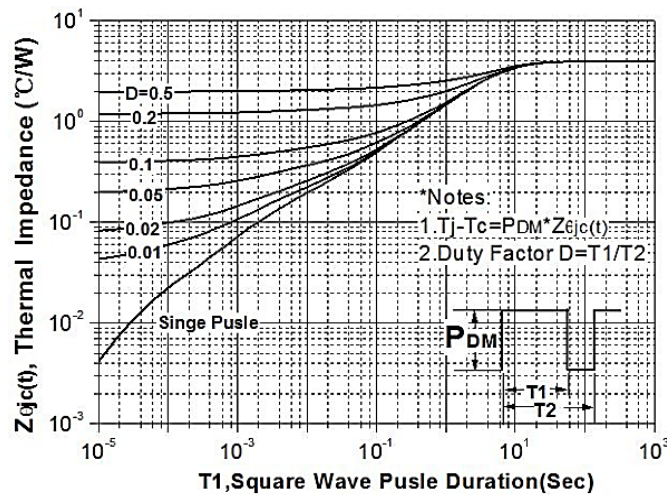
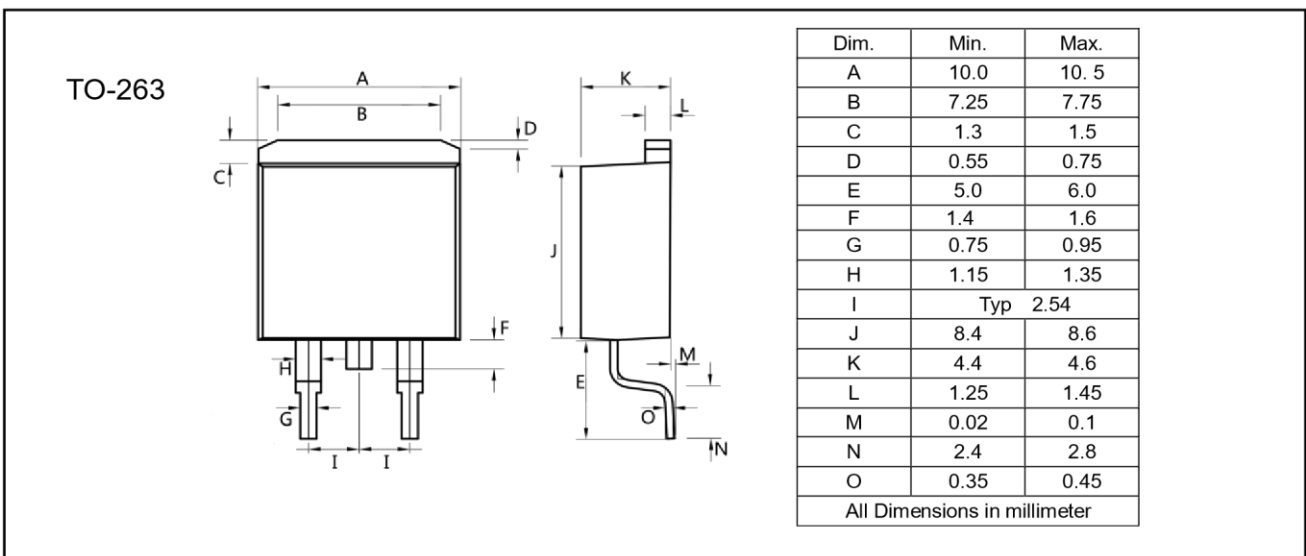
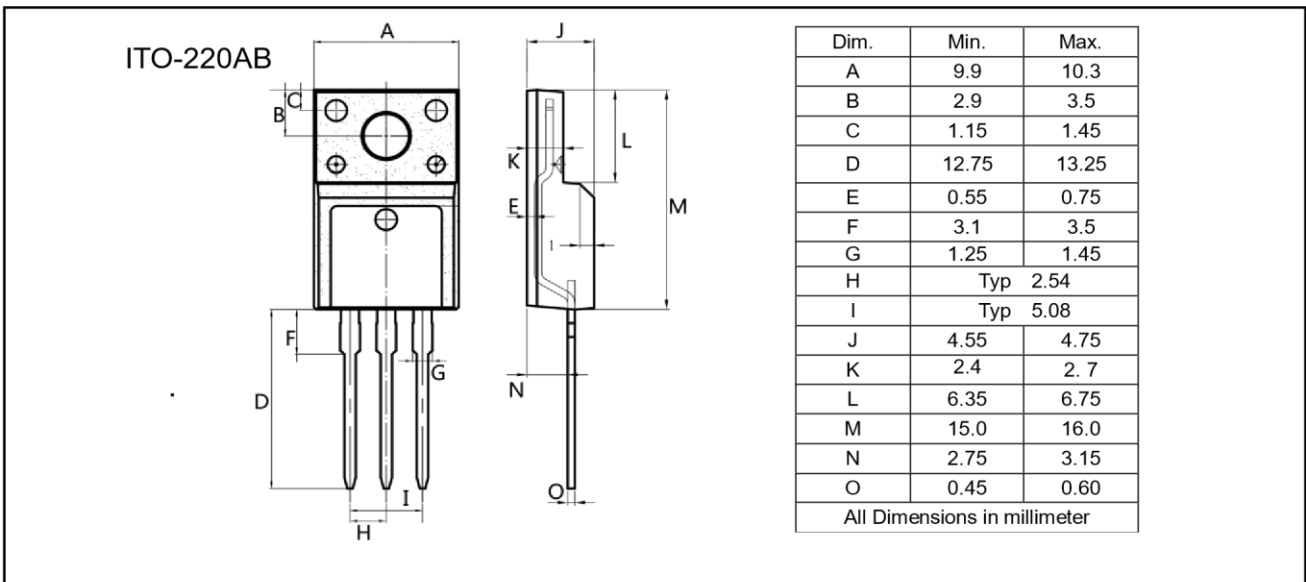
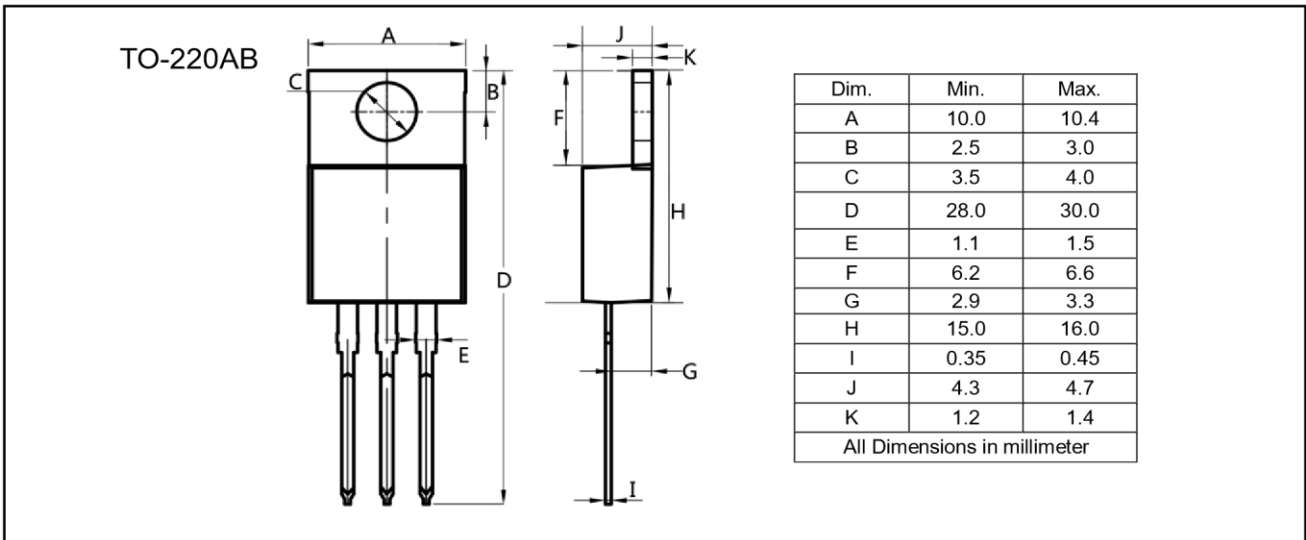


Figure 11. Transient Thermal Response Curve



Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time
Pb device	245°C ±5°C	5sec ±1 sec
Pb-Free device	260°C +0/-5°C	5sec ±1 sec



This integrated circuit can be damaged by ESD. UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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